

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A display device comprising:
an adhesion improving layer comprising one of a metal material and a metal oxide material over and in contact with one substrate of a pair of substrates;
a thin film transistor including:
a gate electrode comprising a conductive material over and in contact with one
~~of substrates~~ the adhesion improving layer;
an island shape gate insulating film including at least one of a silicon nitride layer, a silicon oxynitride layer, and a silicon oxide layer, which is ~~in contact with~~ over the gate electrode;
a semiconductor layer over the island shape gate insulating film; and
source and drain wirings comprising a conductive material, which is connected to the semiconductor layer; and
a pixel electrode connected to the thin film transistor,
wherein an end of the semiconductor layer is provided so as not to protrude from an end of the island shape gate insulating ~~layer~~ film.
2. (Canceled)
3. (Original) A device according to claim 1, further comprising a protective film over the semiconductor layer.
4. (Original) A device according to claim 1, wherein the conductive material of at least one of the gate electrode and the source and drain wirings contains one selected from the group consisting of Ag, Au, Cu, W, and Al as a main component.
5. (Original) A device according to claim 1, wherein the thin film transistor can be operated at an electric field effect mobility of 1 cm²/V·sec to 15 cm²/V·sec, and the

semiconductor layer of the thin film transistor contains hydrogen and halogen, and a semiconductor having a crystal structure.

6. (Currently Amended) A device according to claim 1, wherein the display device is a liquid crystal display device and the substrates sandwich a liquid crystal layer.

7. (Original) A device according to claim 1, wherein the display device is mounted in one of a television receiver, a personal computer, a cellular phone, an information display, and an advertising board.

8. (Currently Amended) A display device comprising:
an adhesion improving layer comprising one of a metal material and a metal oxide material over and in contact with one substrate of a pair of substrates;

a thin film transistor including:

a gate electrode comprising a conductive material over and in contact with~~one of substrates~~ the adhesion improving layer;

an island shape gate insulating film including at least one of a silicon nitride layer, a silicon oxynitride layer, and a silicon oxide layer, which is ~~in contact with~~ over the gate electrode;

a semiconductor layer over the island shape gate insulating film; and

source and drain wirings comprising a conductive material, which is connected to the semiconductor layer; and

a pixel electrode connected to the thin film transistor,

wherein an end of the semiconductor layer is provided so as to coincide with an end of the island shape gate insulating layer film.

9. (Canceled)

10. (Original) A device according to claim 8, further comprising a protective film over the semiconductor layer.

11. (Original) A device according to claim 8, wherein the conductive material of at least one of the gate electrode and the source and drain wirings contains one selected from the group consisting of Ag, Au, Cu, W, and Al as a main component.

12. (Original) A device according to claim 8, wherein the thin film transistor can be operated at an electric field effect mobility of $1 \text{ cm}^2/\text{V}\cdot\text{sec}$ to $15 \text{ cm}^2/\text{V}\cdot\text{sec}$, and the semiconductor layer of the thin film transistor contains hydrogen and halogen, and a semiconductor having a crystal structure.

13. (Currently Amended) A device according to claim 8, wherein the display device is a liquid crystal display device and the substrates sandwich a liquid crystal layer.

14. (Original) A device according to claim 8, wherein the display device is mounted in one of a television receiver, a personal computer, a cellular phone, an information display, and an advertising board.

15-67. (Canceled)

68. (New) A display device comprising:

an adhesion improving layer comprising one of a metal material and a metal oxide material over and in contact with one substrate of a pair of substrates;

a thin film transistor including:

a gate electrode comprising a conductive material over and in contact with the adhesion improving layer;

an island shape gate insulating film including at least one of a silicon nitride layer, a silicon oxynitride layer, and a silicon oxide layer, which is over the gate electrode;

a semiconductor layer over the island shape gate insulating film; and

source and drain wirings comprising a conductive material, which is connected to the semiconductor layer; and

a pixel electrode connected to the thin film transistor.

69. (New) A display device comprising:

an adhesion improving layer formed of a metal material over and in contact with one substrate of a pair of substrates;

a thin film transistor including:

a gate electrode comprising a conductive material over and in contact with the adhesion improving layer;

an island shape gate insulating film including at least one of a silicon nitride layer, a silicon oxynitride layer, and a silicon oxide layer, which is over the gate electrode;

a semiconductor layer over the island shape gate insulating film; and

source and drain wirings comprising a conductive material, which is connected to the semiconductor layer; and

a pixel electrode connected to the thin film transistor,

wherein an end of the semiconductor layer is provided so as not to protrude from an end of the island shape gate insulating film.

70. (New) A display device comprising:

an adhesion improving layer formed of a metal material over and in contact with one substrate of a pair of substrates;

a thin film transistor including:

a gate electrode comprising a conductive material over and in contact with the adhesion improving layer;

an island shape gate insulating film including at least one of a silicon nitride layer, a silicon oxynitride layer, and a silicon oxide layer, which is over the gate electrode;

a semiconductor layer over the island shape gate insulating film; and

source and drain wirings comprising a conductive material, which is connected to the semiconductor layer; and

a pixel electrode connected to the thin film transistor,

wherein an end of the semiconductor layer is provided so as to coincide with an end of the island shape gate insulating film.

71. (New) A display device comprising:

an adhesion improving layer formed of a metal material over and in contact with one substrate of a pair of substrates;

a thin film transistor including:

a gate electrode comprising a conductive material over and in contact with the adhesion improving layer;

an island shape gate insulating film including at least one of a silicon nitride layer, a silicon oxynitride layer, and a silicon oxide layer, which is over the gate electrode;

a semiconductor layer over the island shape gate insulating film; and

source and drain wirings comprising a conductive material, which is connected to the semiconductor layer; and

a pixel electrode connected to the thin film transistor.

72. (New) A device according to claim 68, further comprising a protective film over the semiconductor layer.

73. (New) A device according to claim 68, wherein the conductive material of at least one of the gate electrode and the source and drain wirings contains one selected from the group consisting of Ag, Au, Cu, W, and Al as a main component.

74. (New) A device according to claim 68, wherein the thin film transistor can be operated at an electric field effect mobility of $1 \text{ cm}^2/\text{V}\cdot\text{sec}$ to $15 \text{ cm}^2/\text{V}\cdot\text{sec}$, and the semiconductor layer of the thin film transistor contains hydrogen and halogen, and a semiconductor having a crystal structure.

75. (New) A device according to claim 68, wherein the display device is a liquid crystal display device and the substrates sandwich a liquid crystal layer.

76. (New) A device according to claim 68, wherein the display device is mounted in one of a television receiver, a personal computer, a cellular phone, an information display, and an advertising board.

77. (New) A device according to claim 68, an end of the adhesion improving layer is provided so as to coincide with an end of the gate electrode.

78. (New) A device according to claim 69, further comprising a protective film over the semiconductor layer.

79. (New) A device according to claim 69, wherein the conductive material of at least one of the gate electrode and the source and drain wirings contains one selected from the group consisting of Ag, Au, Cu, W, and Al as a main component.

80. (New) A device according to claim 69, wherein the thin film transistor can be operated at an electric field effect mobility of $1 \text{ cm}^2/\text{V}\cdot\text{sec}$ to $15 \text{ cm}^2/\text{V}\cdot\text{sec}$, and the semiconductor layer of the thin film transistor contains hydrogen and halogen, and a semiconductor having a crystal structure.

81. (New) A device according to claim 69, wherein the display device is a liquid crystal display device and the substrates sandwich a liquid crystal layer.

82. (New) A device according to claim 69, wherein the display device is mounted in one of a television receiver, a personal computer, a cellular phone, an information display, and an advertising board.

83. (New) A device according to claim 69, an end of the adhesion improving layer is provided so as to coincide with an end of the gate electrode.

84. (New) A device according to claim 70, further comprising a protective film over the semiconductor layer.

85. (New) A device according to claim 70, wherein the conductive material of at least one of the gate electrode and the source and drain wirings contains one selected from the group consisting of Ag, Au, Cu, W, and Al as a main component.

86. (New) A device according to claim 70, wherein the thin film transistor can be operated at an electric field effect mobility of $1 \text{ cm}^2/\text{V}\cdot\text{sec}$ to $15 \text{ cm}^2/\text{V}\cdot\text{sec}$, and the semiconductor layer of the thin film transistor contains hydrogen and halogen, and a semiconductor having a crystal structure.

87. (New) A device according to claim 70, wherein the display device is a liquid crystal display device and the substrates sandwich a liquid crystal layer.

88. (New) A device according to claim 70, wherein the display device is mounted in one of a television receiver, a personal computer, a cellular phone, an information display, and an advertising board.

89. (New) A device according to claim 70, an end of the adhesion improving layer is provided so as to coincide with an end of the gate electrode.

90. (New) A device according to claim 71, further comprising a protective film over the semiconductor layer.

91. (New) A device according to claim 71, wherein the conductive material of at least one of the gate electrode and the source and drain wirings contains one selected from the group consisting of Ag, Au, Cu, W, and Al as a main component.

92. (New) A device according to claim 71, wherein the thin film transistor can be operated at an electric field effect mobility of $1 \text{ cm}^2/\text{V}\cdot\text{sec}$ to $15 \text{ cm}^2/\text{V}\cdot\text{sec}$, and the semiconductor layer of the thin film transistor contains hydrogen and halogen, and a semiconductor having a crystal structure.

93. (New) A device according to claim 71, wherein the display device is a liquid crystal display device and the substrates sandwich a liquid crystal layer.

94. (New) A device according to claim 71, wherein the display device is mounted in one of a television receiver, a personal computer, a cellular phone, an information display, and an advertising board.

95. (New) A device according to claim 71, an end of the adhesion improving layer is provided so as to coincide with an end of the gate electrode.

96. (New) A device according to claim 1, an end of the adhesion improving layer is provided so as to coincide with an end of the gate electrode.

97. (New) A device according to claim 8, an end of the adhesion improving layer is provided so as to coincide with an end of the gate electrode.